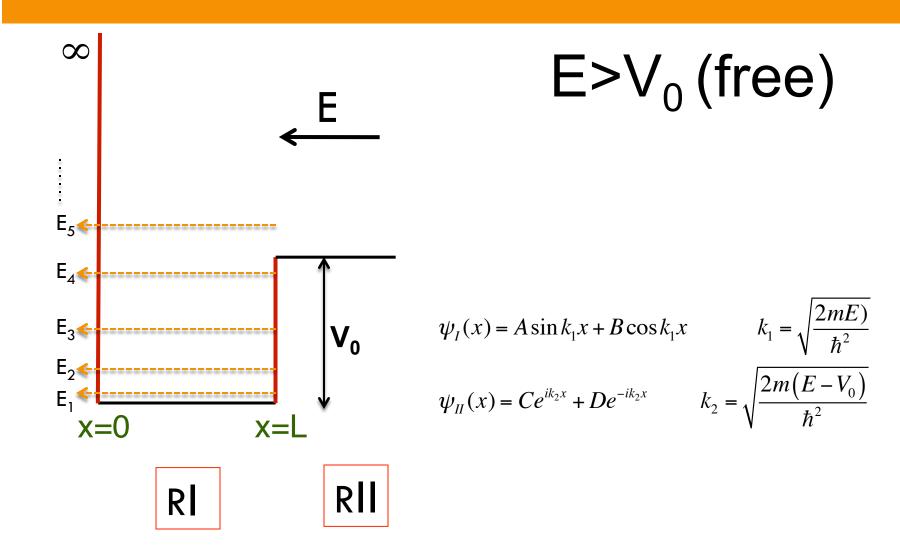
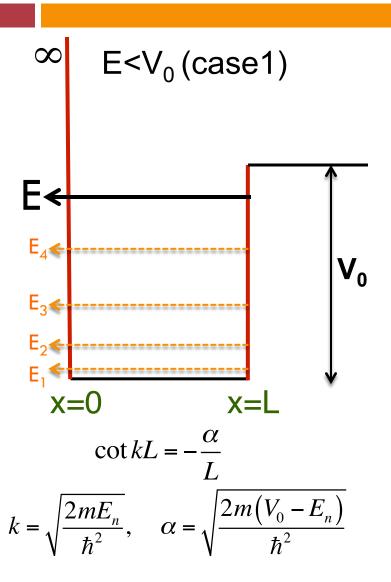
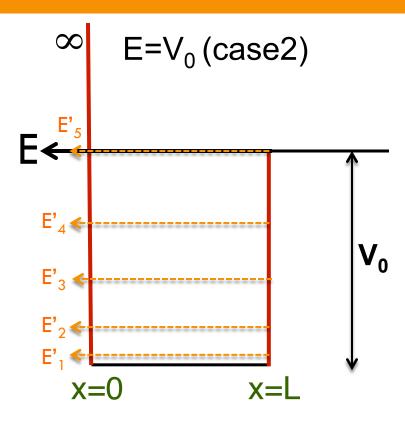
Semi-infinite potential well and Potential Barrier: Quantum Tunneling

Semi-infinite rectangular potential well (contd.)



Bound States

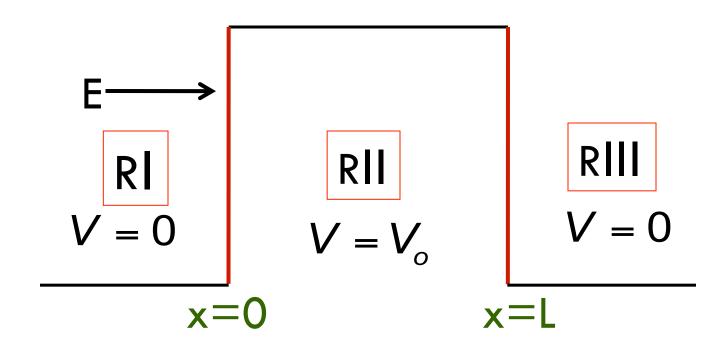




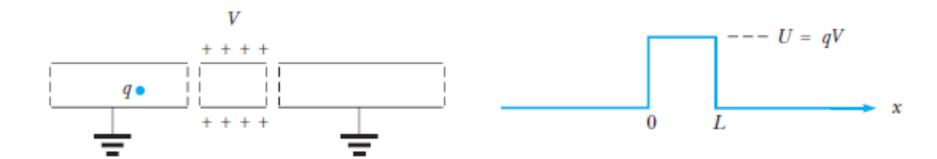
$$\cos k \mathcal{L} = 0, \ \mathcal{E}_{n}' = \frac{\hbar^{2} \left[(2n+1) \frac{\pi}{2} \right]^{2}}{2m \mathcal{L}^{2}}$$

Quantum mechanical tunneling through a potential barrier

$$V(x) = V_o \text{ for } 0 < x < L$$
$$= 0 \text{ for } x < 0 \text{ or } x > L$$



Electron encountering a barrier



$$\frac{d^{2}\psi_{I}(x)}{dx^{2}} + \frac{2m}{\hbar^{2}}E\psi_{I}(x) = 0 \qquad \text{Region 1}$$

$$\frac{d^{2}\psi_{II}(x)}{dx^{2}} + \frac{2m}{\hbar^{2}}(E - V_{0})\psi_{II}(x) = 0 \qquad \text{Region 2}$$

$$\frac{d^{2}\psi_{III}(x)}{dx^{2}} + \frac{2m}{\hbar^{2}}E\psi_{III}(x) = 0 \qquad \text{Region 3}$$

Note that E is positive and (E-V₀) is negative

$$\psi_I(x) = Ae^{ikx} + Be^{-ikx}$$

$$k = \sqrt{\frac{2mE}{\hbar^2}}$$

$$\psi_{II}(x) = Ce^{\alpha x} + De^{-\alpha x}$$

$$\psi_{II}(x) = Ce^{\alpha x} + De^{-\alpha x} \qquad \alpha = \sqrt{\frac{2m(V_0 - E)}{\hbar^2}}$$

RIII
$$\psi_{III}(x) = Fe^{ikx} + Ge^{-ikx}$$

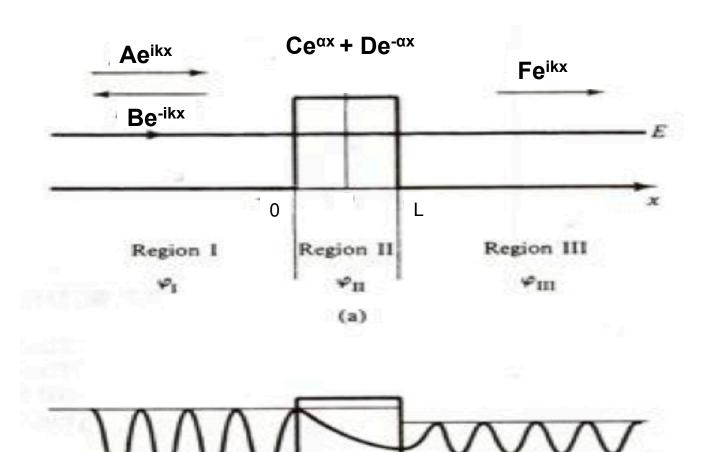
$$k = \sqrt{\frac{2mE}{\hbar^2}}$$

In region 1, there is the original wave and the reflected wave. Hence both A and B are non zero.

In region two, the ends do not go to infinity and hence both C and D survive.

In region 3, since no reflection at x=+∞, G=0

Pictorial Representation



Boundary Conditions yields

$$G = 0$$

$$A + B = C + D$$

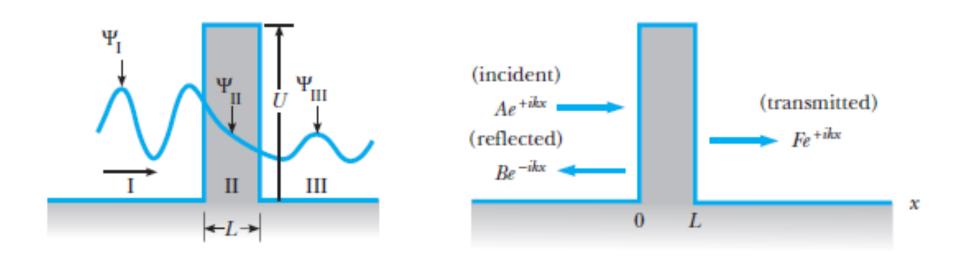
$$ik(A - B) = \alpha(C - D)$$

$$Ce^{\alpha L} + De^{-\alpha L} = Fe^{ikL}$$

$$\alpha(Ce^{\alpha L} - De^{-\alpha L}) = Fike^{ikL}$$

$$\frac{1}{T} = \left|\frac{A}{F}\right|^2 = 1 + \frac{1}{4}\left(\frac{\alpha}{k} + \frac{k}{\alpha}\right)^2 \sinh^2 \alpha L$$

Quantum Mechanical Tunneling



Dominant term determining the tunneling is $e^{-\alpha x}$

Example:

Consider

- □An electron of E=1 eV.
- □Potential barrier of V_0 =2eV and L=1 nm
- The probability that the electron will tunnel through the barrier is about 80%!!!

Consequences

If E<V₀, the beam gets reflected back. But the wave gets attenuated in the region II and then enters the region III. In region III, it travels with the same wave length (energy), but with less amplitude.

Limiting Case

$$\mathcal{T} = \left[1 + \frac{1}{4} \left(\frac{\alpha}{k} + \frac{k}{\alpha} \right)^2 \sinh^2 \alpha \mathcal{L} \right]^{-1} = \left[1 + \frac{V_0^2}{4 \mathcal{E}(V_0 - \mathcal{E})} \sinh^2 \alpha \mathcal{L} \right]^{-1}$$

If $\alpha L >>> 1$ (E << $< V_0$), then $\sinh(\alpha L) \approx e^{\alpha L}/2$

$$\mathcal{T} = \left[\frac{16E}{V_0} \left(1 - \frac{E}{V_0} \right) e^{-2\alpha L} \right]$$

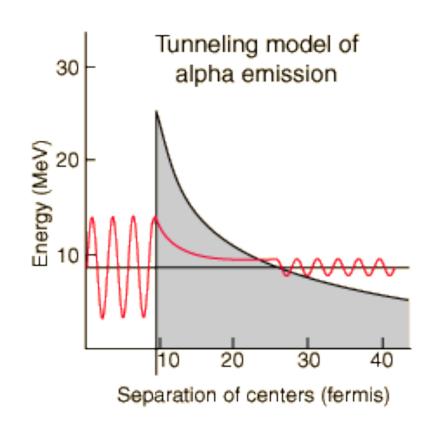
Transmission probability (T) decreases with

- (i) increasing the width of the barrier (L)
- (ii) decreasing the energy E w.r.to V_0

Experimental evidences for tunneling

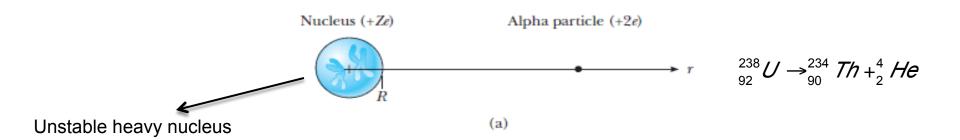
1. Gamow's theory of Alpha decay

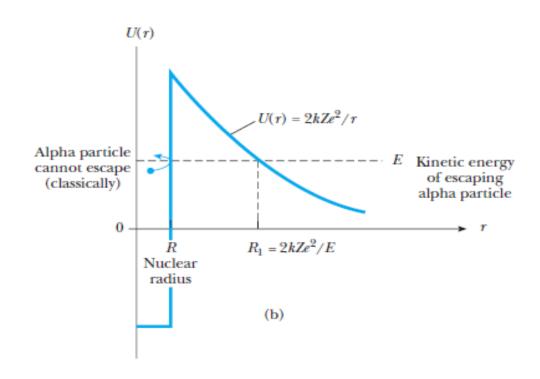
Though the energy (E) of nucleons (α -particle) is smaller than the potential barrier produced by the nuclear forces (V_0), the alpha particle escapes the nucleus because of tunneling effect



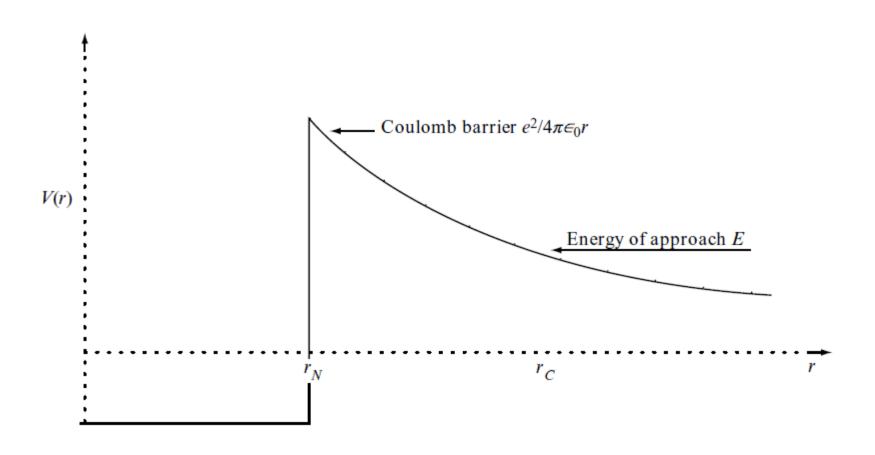
 $\Delta E. \Delta t \ge h/4\pi$

Alpha decay (contd.)



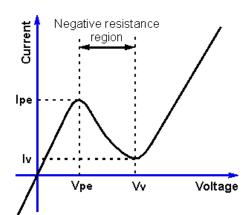


2. Tunneling of protons: energy of sun



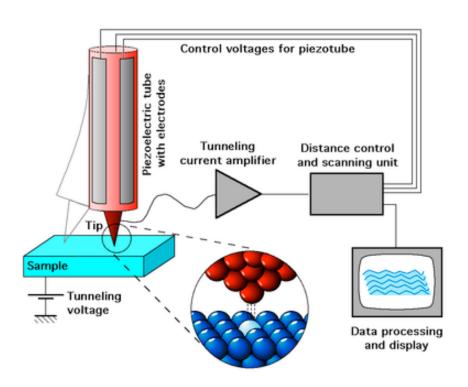
3. Tunnel diode

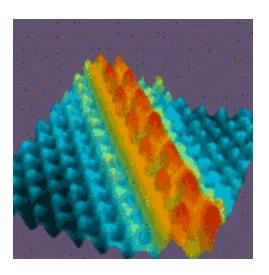
- Ordinary pn diodes depend on diffusion current and hence the switching speed is very low.
- A heavily doped pn junction has a very thin depletion layer and hence has tunneling current.
- The tunneling current can be controlled by changing the potential barrier (the step) by applied voltage.
- □ Very high switching frequencies (~ GHz).

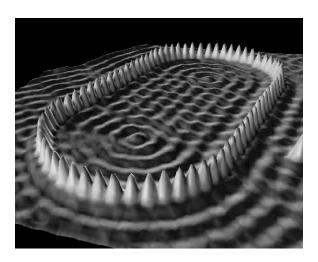


4. Scanning tunneling microscope

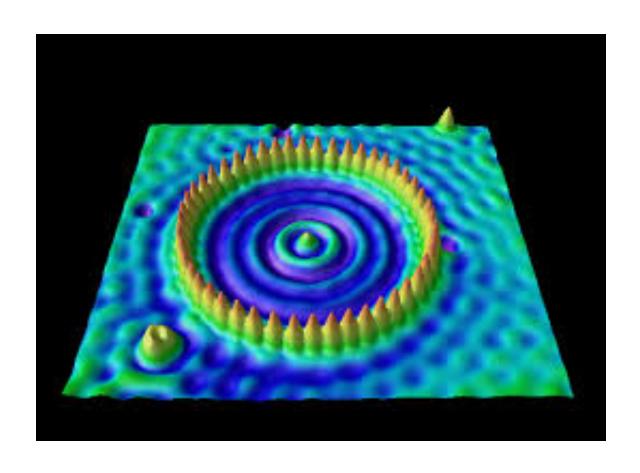
Atomic resolution of surfaces Nobel Prize in Physics (1986)







Fe atoms on Cu surface STM



Graphite atoms seen by STM

